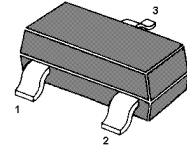
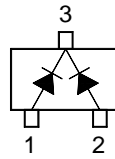


SB495D

Schottky Barrier Diode



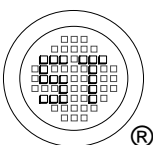
Marking Code: **D3Q**
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	40	V
Reverse Voltage	V_R	25	V
Forward Current	$I_{F(AV)}$	350	mA
Peak Forward Surge Current (8.3 ms)	I_{FSM}	1.5	A
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$ at $I_F = 200\text{ mA}$	V_F	- -	0.32 0.55	V
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$	$V_{(BR)R}$	40	-	-
Reverse Current at $V_R = 25\text{ V}$	I_R	-	70	μA
Total Capacitance at $V_R = 0$, $f = 1\text{ MHz}$	C_{tot}	-	50	pF



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FIG 1 Typical Forward Characteristics

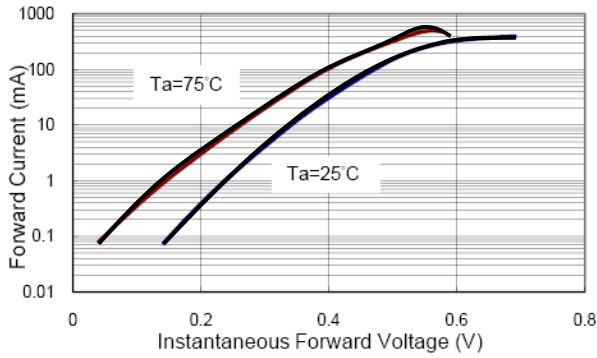


FIG 2 Reverse Current vs Reverse Voltage

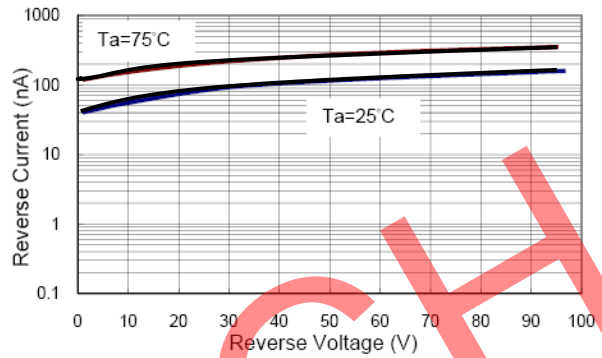


FIG 3 Admissible Power Dissipation Curve

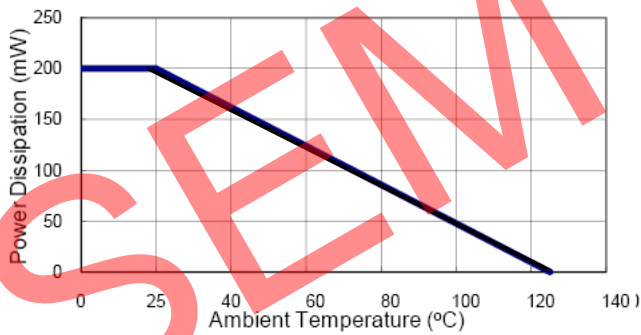


FIG 4 Typical Junction Capacitance

